

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

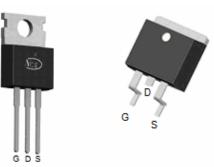
- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

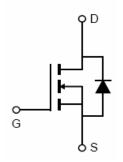
General Features

- V_{DS} =85V, I_D =100A $R_{DS(ON)}$ =4.8m Ω , typical (TO-220)@ V_{GS} =10V $R_{DS(ON)}$ =4.6m Ω , typical (TO-263)@ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!







Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP055N85	NCEP055N85	TO-220	-	-	-
NCEP055N85D	NCEP055N85D	TO-263	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	85	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	100	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	73.5	Α
Pulsed Drain Current	I _{DM}	400	Α
Maximum Power Dissipation	P _D	125	W
Derating factor		0.83	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	580	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	$^{\circ}$



NCEP055N85, NCEP055N85D

Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	$R_{ heta JC}$	1.2	°C/W	
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Electrical Characteristics (T_C=25°C unless otherwise noted)

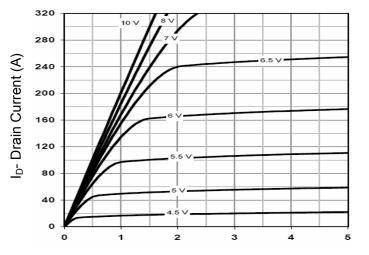
Parameter	Symbol	ool Condition		Min	Тур	Max	Unit
Off Characteristics				•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA		85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS}	_S =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _E	os=0V	-	-	±100	nA
On Characteristics (Note 3)				· ·	l.		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=2$	50μΑ	2.0	3.0	4.0	V
Danier Courses Our Otata Basistana	-	V _{GS} =10V, I _D =50A	TO-220	-	4.8	5.5	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}		TO-263		4.6	5.5	mΩ
Forward Transconductance	g FS	$V_{DS}=5V,I_{D}=$	50A		60	-	S
Dynamic Characteristics (Note4)				•			
Input Capacitance	C _{lss}	V _{DS} =40V,V _{GS} =0V, F=1.0MHz		-	3600	-	PF
Output Capacitance	Coss			-	570	-	PF
Reverse Transfer Capacitance	C _{rss}			-	30	-	PF
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}			-	18	-	nS
Turn-on Rise Time	t _r	V_{DD} =40V, I_{D} =50A V_{GS} =10V, R_{G} =1.6Ω		-	55	-	nS
Turn-Off Delay Time	t _{d(off)}			-	38	-	nS
Turn-Off Fall Time	t _f			-	10	-	nS
Total Gate Charge	Qg	\/ -40\/.	FO A	-	56	-	nC
Gate-Source Charge	Q_{gs}	$V_{DS}=40V,I_{D}=$	•	-	21		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V		-	13		nC
Drain-Source Diode Characteristics				•	•		
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =50A		-		1.2	V
Diode Forward Current (Note 2)	Is			-	-	100	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S		-	64	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)		-	130	-	nC

Notes:

- ${\it 1. Repetitive Rating: Pulse width \ limited \ by \ maximum \ junction \ temperature.}$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=40V,V_G=10V,L=0.5mH,Rg=25 Ω

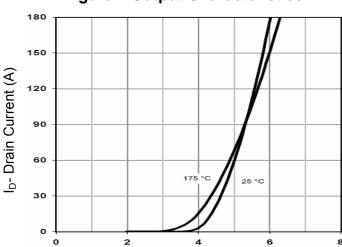


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

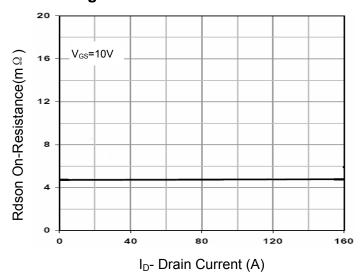
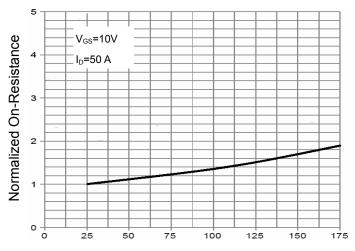


Figure 3 Rdson- Drain Current



T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature

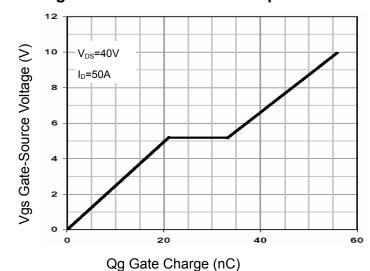
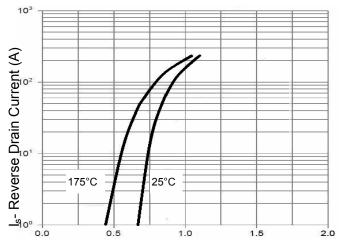


Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



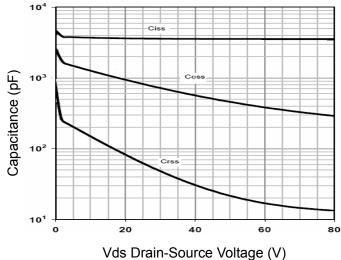


Figure 7 Capacitance vs Vds

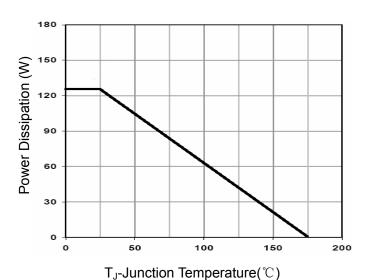


Figure 9 Power De-rating

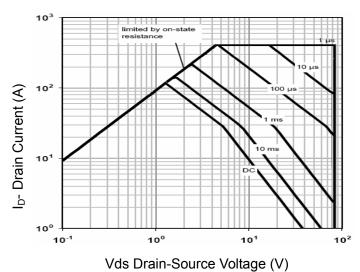


Figure 8 Safe Operation Area

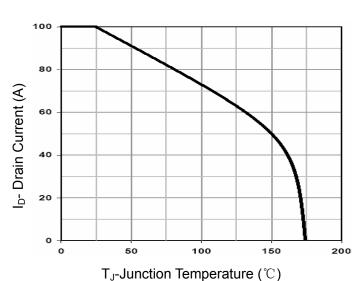


Figure 10 Current De-rating

V1.0

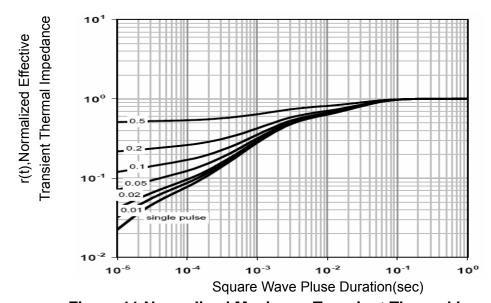
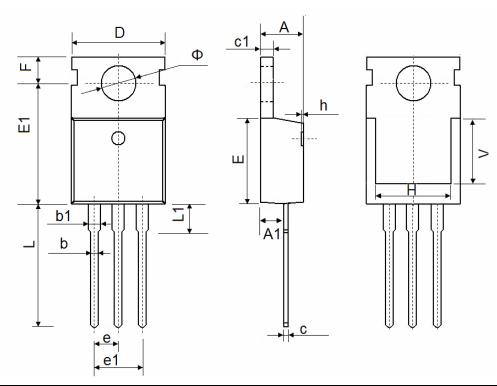


Figure 11 Normalized Maximum Transient Thermal Impedance



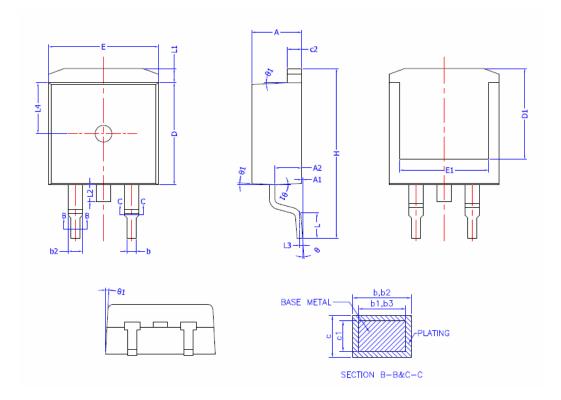
TO-220-3L Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.90	6.900 REF. 0.276 REF.		REF.	
Ф	3.400	3.800	0.134	0.150	



TO-263-2L Package Information



COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2,20	2,40	2,60	
b	0,76		0,89	
b1	0,75	0,80	0,85	
b2	1,23	_	1,37	
b3	1,22	1,27	1,32	
С	0,47		0,60	
c1	0.46	0,51	0.56	
c2	1,25	1.30	1,35	
D	9.10	9.20	9,30	
D1	8.00	_	_	
E	9.80	9.90	10.00	
E1	7.80	_	_	
е	2.	54 BSC		
Н	14.90	15.30	15.70	
L	2.00	2.30	2.60	
L1	1.17	1.27	1.40	
L1 L2	_	_	1,75	
L3	0.25BSC			
L4	4.60 REF			
θ	0°	_	8°	
θ1	1°	3°	5°	

NCEP055N85, NCEP055N85D



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